

• General Description

The ZM930P06D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

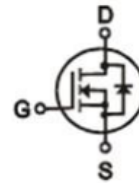
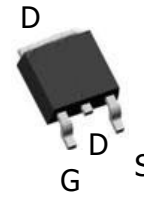
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Ordering Information:

Part NO.	ZM930P06D
Marking	ZM930P06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

• Absolute Maximum Ratings (T_c =25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_D@TC=25^{\circ}C$	-12	A
	$I_D@TC=75^{\circ}C$	-9	A
	$I_D@TC=100^{\circ}C$	7.5	A
Pulsed Drain Current ①	I_{DM}	-30	A
Total Power Dissipation(TC=25°C)	$P_D@TC=25^{\circ}C$	50	W
Total Power Dissipation(TA=25°C)	$P_D@TA=25^{\circ}C$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C
Single Pulse Avalanche Energy	E_{AS}	40	mJ

• Product Summary

 $V_{DS} = -60V$
 $R_{DS(ON)} = 93m\Omega$
 $I_D = -12A$


TO-252



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	2.4	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	65	° C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-12A		93	120	mΩ
		V _{GS} =-4.5V, I _D =-10A		128	166	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-2A		10		s
Source-drain voltage	V _{SD}	I _S =-12A			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz	-	650	-	pF
Output capacitance	C _{oss}		-	120	-	
Reverse transfer capacitance	C _{rss}		-	70	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 25V	-	12	-	nC
Gate - Source charge	Q _{gs}	I _D = 5A	-	4	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	6	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Fig.1 Power Dissipation Derating Curve

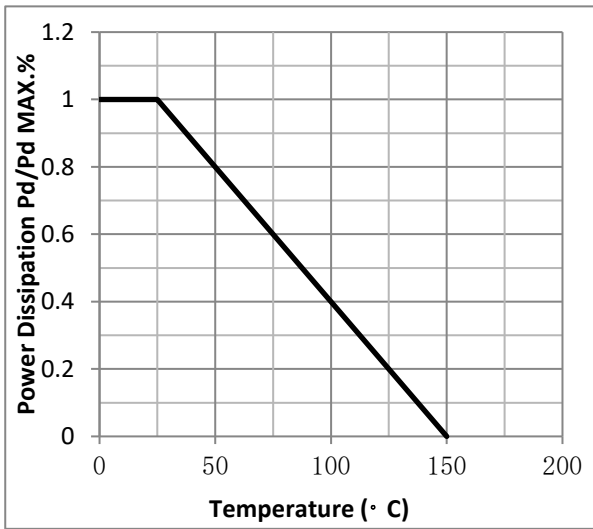


Fig.2 Typical output Characteristics

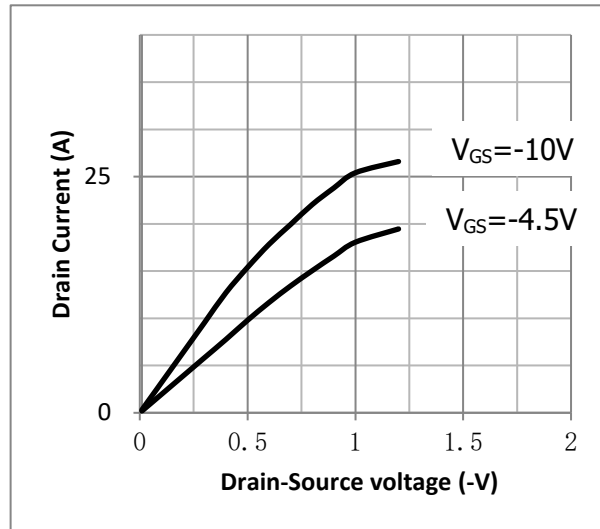


Fig.3 Threshold Voltage V.S Junction Temperature

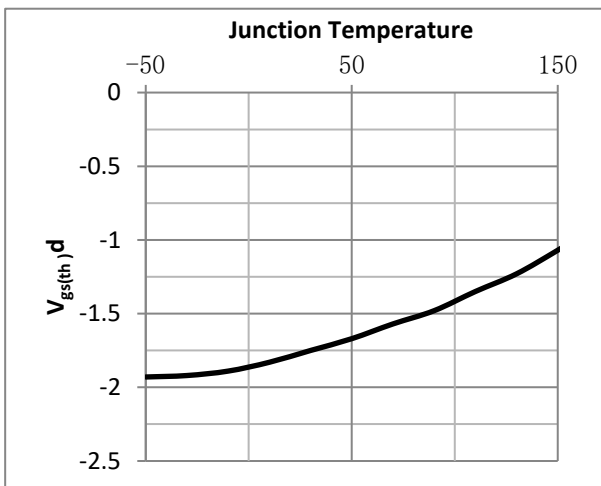


Fig.4 Resistance V.S Drain Current

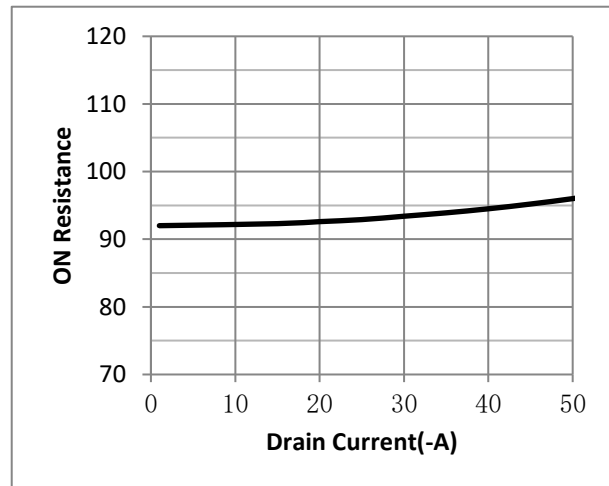


Fig.5 On-Resistance VS Gate Source Voltage

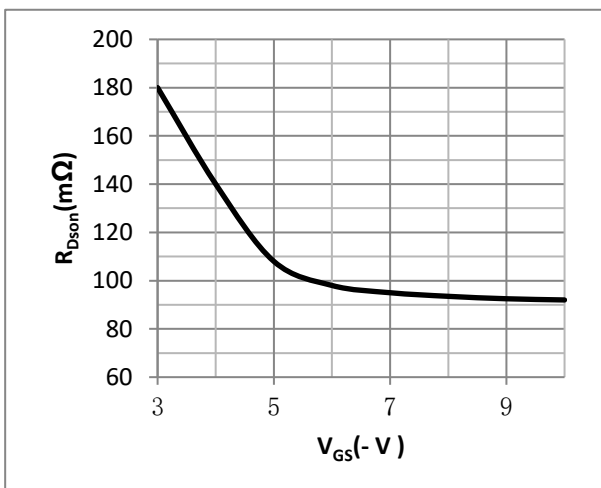


Fig.6 On-Resistance V.S Junction Temperature

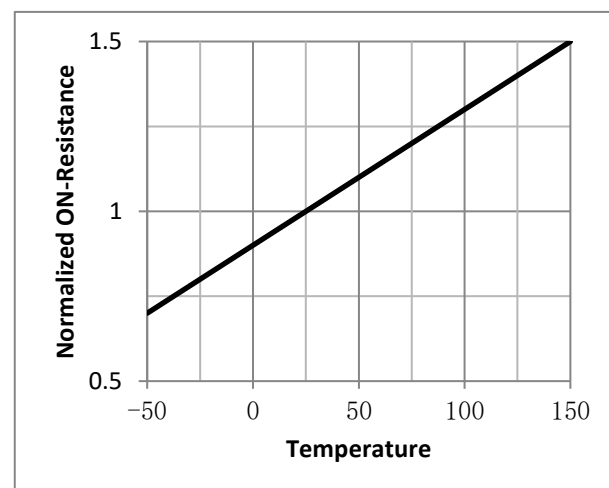


Fig.7 Switching Time Measurement Circuit

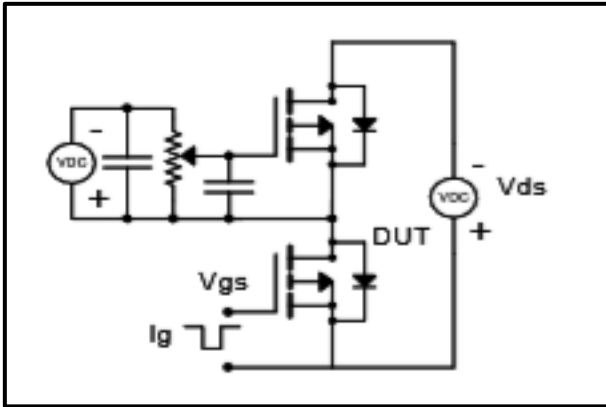


Fig.8 Gate Charge Waveform

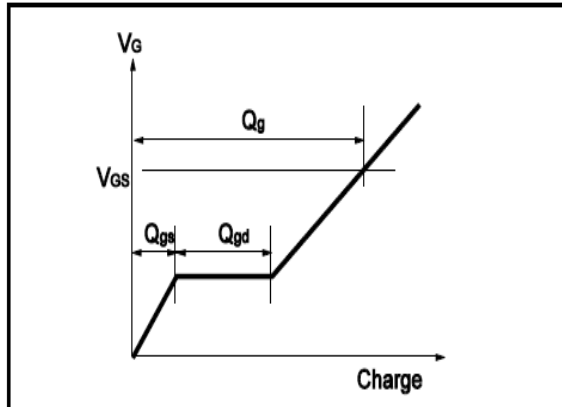


Fig.9 Switching Time Measurement Circuit

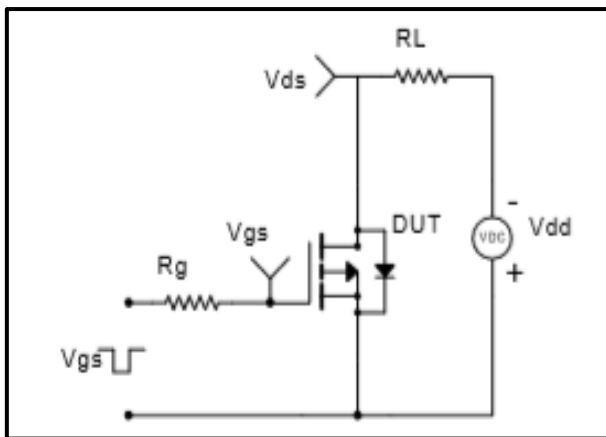


Fig.10 Gate Charge Waveform

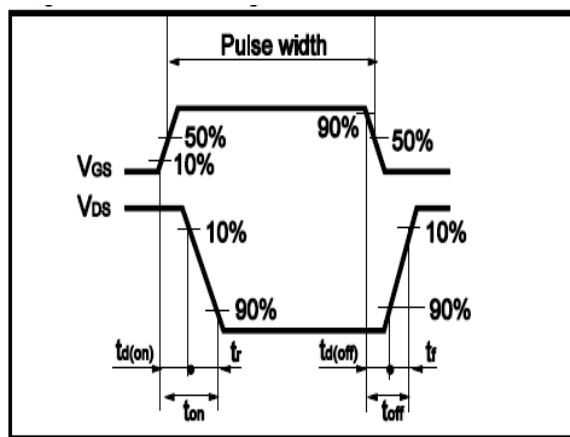


Fig.11 Avalanche Measurement Circuit

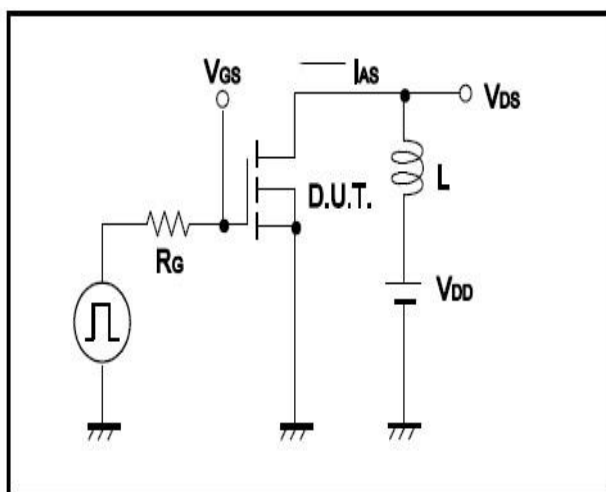
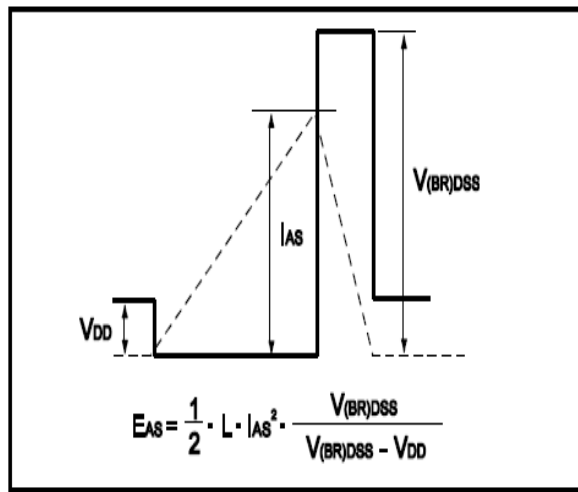


Fig.12 Avalanche Waveform





•Dimensions(TO-252)

Unit: mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

